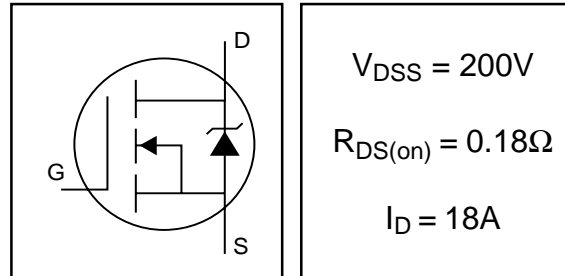


IRF640S/L

HEXFET® Power MOSFET

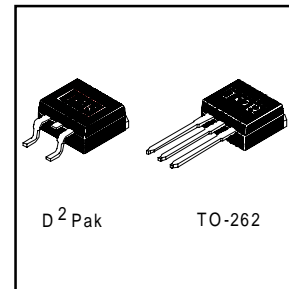
- Surface Mount (IRF640S)
- Low-profile through-hole (IRF640L)
- Available in Tape & Reel (IRF640S)
- Dynamic dv/dt Rating
- 150°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combinations of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application. The through-hole version (IRF640L) is available for low-profile applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{\text{⑤}}$	18	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}^{\text{⑤}}$	11	
I_{DM}	Pulsed Drain Current ①⑤	72	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	3.1	W
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	130	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②⑤	580	mJ
I_{AR}	Avalanche Current①	18	A
E_{AR}	Repetitive Avalanche Energy①	13	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

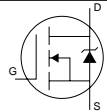
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)**	—	40	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.29	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.18	Ω	$V_{GS} = 10V, I_D = 11A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	6.7	—	—	S	$V_{DS} = 50V, I_D = 11A$ ⑤
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 160V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	70	nC	$I_D = 18A$
Q_{gs}	Gate-to-Source Charge	—	—	13		$V_{DS} = 160V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	39		$V_{GS} = 10V$, See Fig. 6 and 13 ④ ⑤
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = 100V$
t_r	Rise Time	—	51	—		$I_D = 18A$
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		$R_G = 9.1\Omega$
t_f	Fall Time	—	36	—		$R_D = 5.4\Omega$, See Fig. 10 ④ ⑤
L_S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	—	1300	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	430	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	130	—		$f = 1.0\text{MHz}$, See Fig. 5 ⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	18	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ① ⑤	—	—	72		
V_{SD}	Diode Forward Voltage	—	—	2.0	V	$T_J = 25^\circ\text{C}, I_S = 18A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	300	610	ns	$T_J = 25^\circ\text{C}, I_F = 18A$
Q_{rr}	Reverse Recovery Charge	—	3.4	7.1	μC	$di/dt = 100A/\mu s$ ④ ⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 50V$, starting $T_J = 25^\circ\text{C}$, $L = 2.7\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 18A$. (See Figure 12)
- ③ $I_{SD} \leq 18A$, $di/dt \leq 150A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ Uses IRF640 data and test conditions

** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

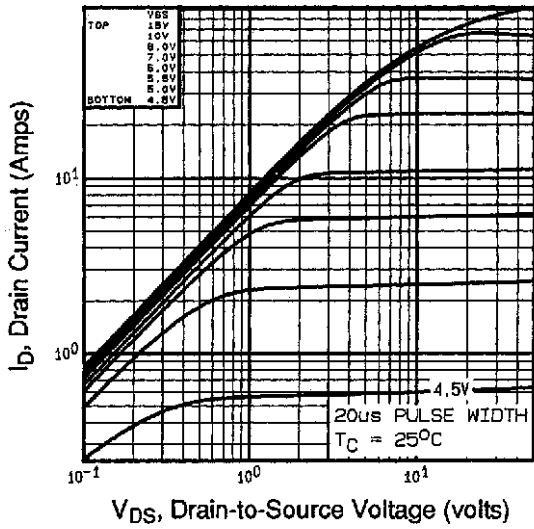


Fig 1. Typical Output Characteristics,
 $T_J = 25^\circ\text{C}$

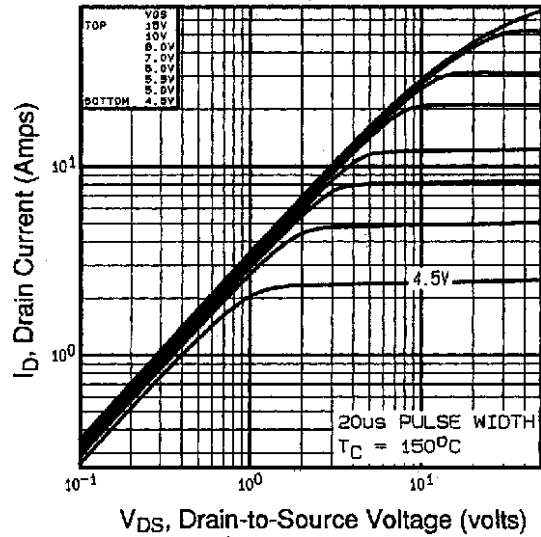


Fig 2. Typical Output Characteristics,
 $T_J = 175^\circ\text{C}$

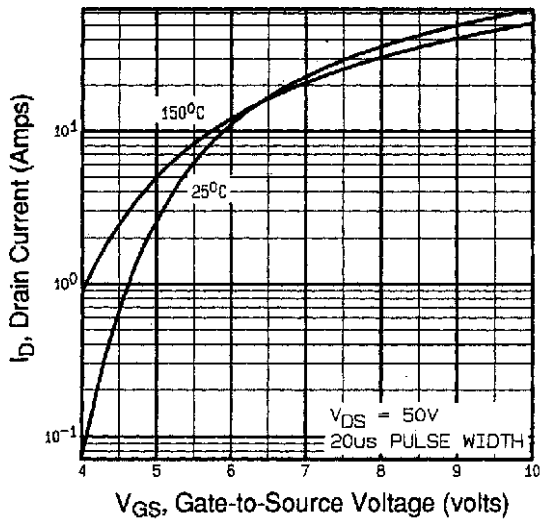


Fig 3. Typical Transfer Characteristics

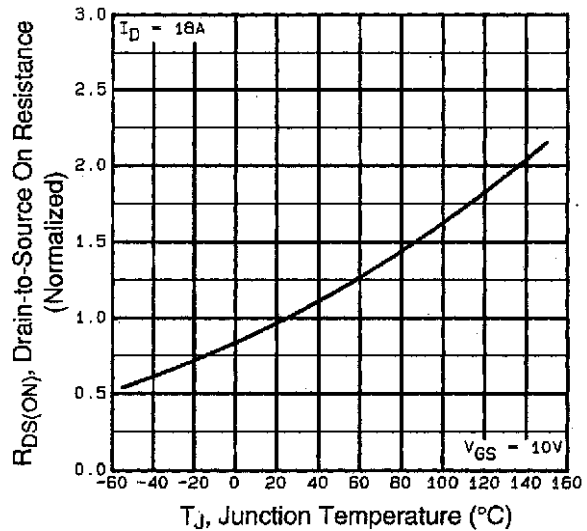


Fig 4. Normalized On-Resistance
Vs. Temperature

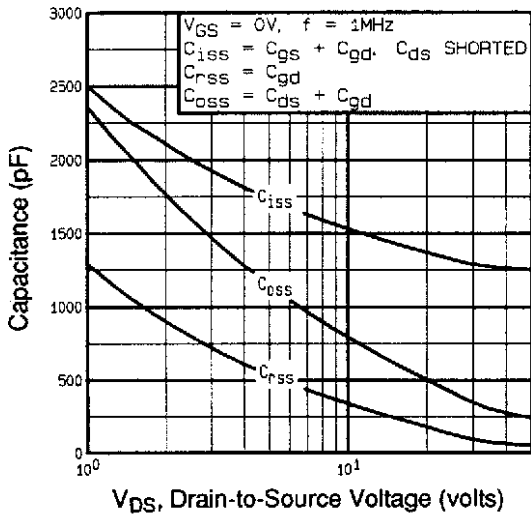


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

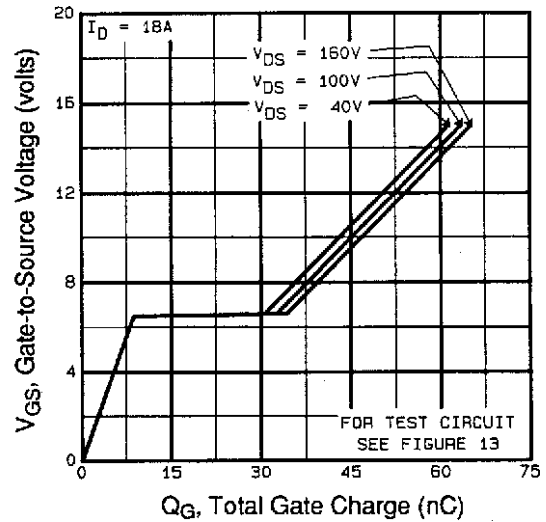


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

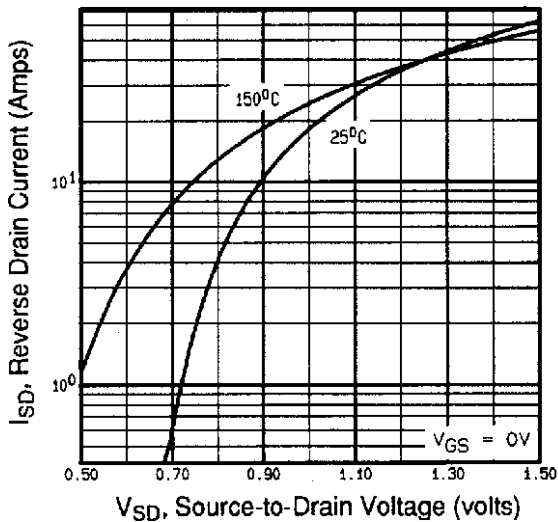


Fig 7. Typical Source-Drain Diode Forward Voltage

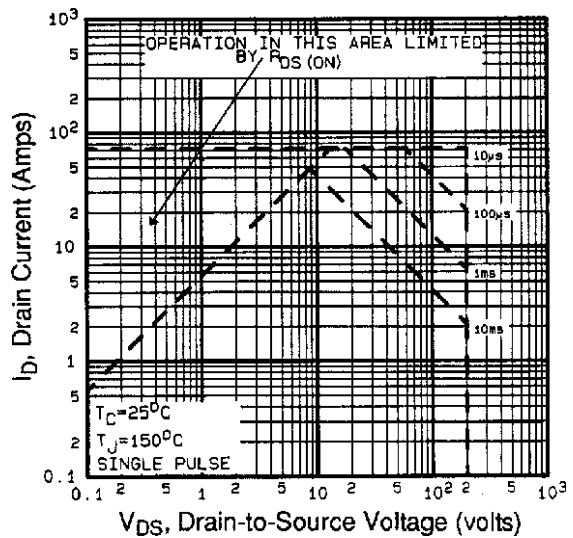


Fig 8. Maximum Safe Operating Area

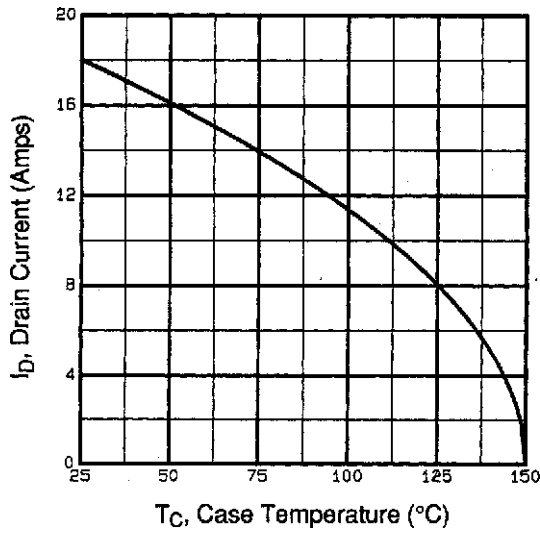


Fig 9. Maximum Drain Current Vs. Case Temperature

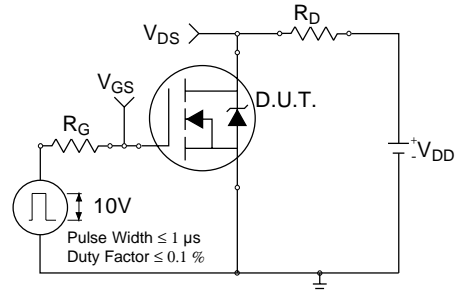


Fig 10a. Switching Time Test Circuit

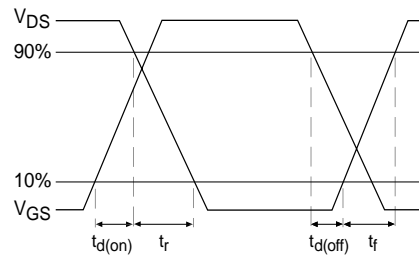


Fig 10b. Switching Time Waveforms

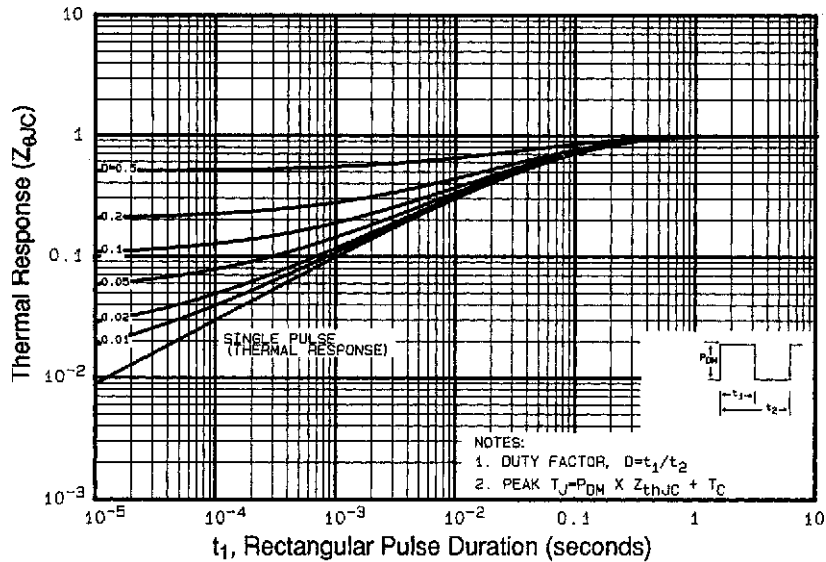


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRF640S/L

International
IR Rectifier

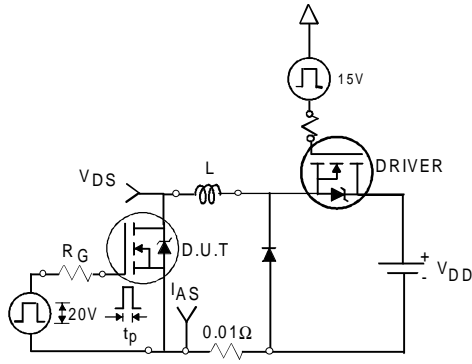


Fig 12a. Unclamped Inductive Test Circuit

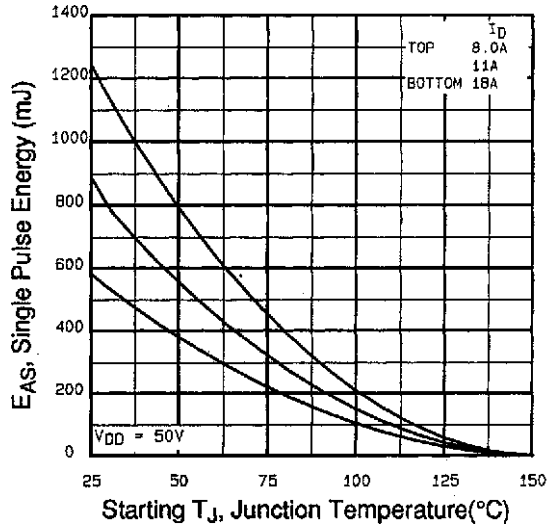


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

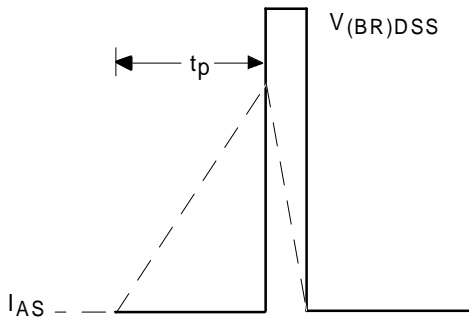


Fig 12b. Unclamped Inductive Waveforms

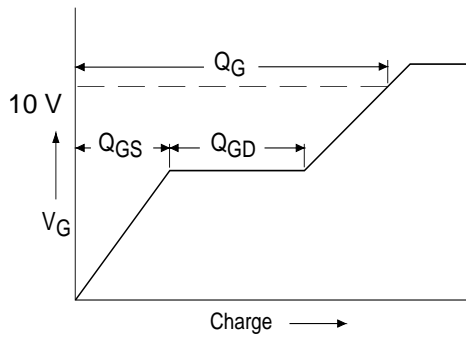


Fig 13a. Basic Gate Charge Waveform

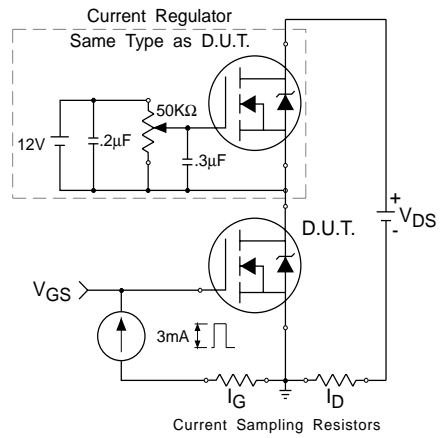
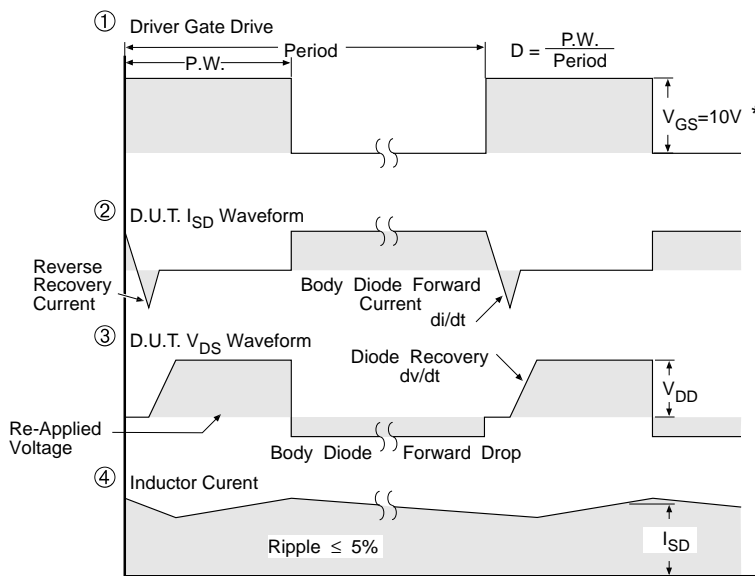
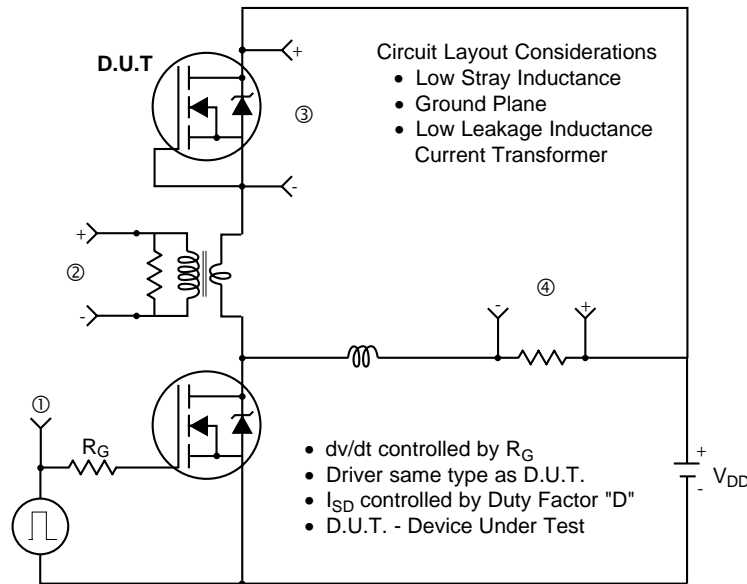


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



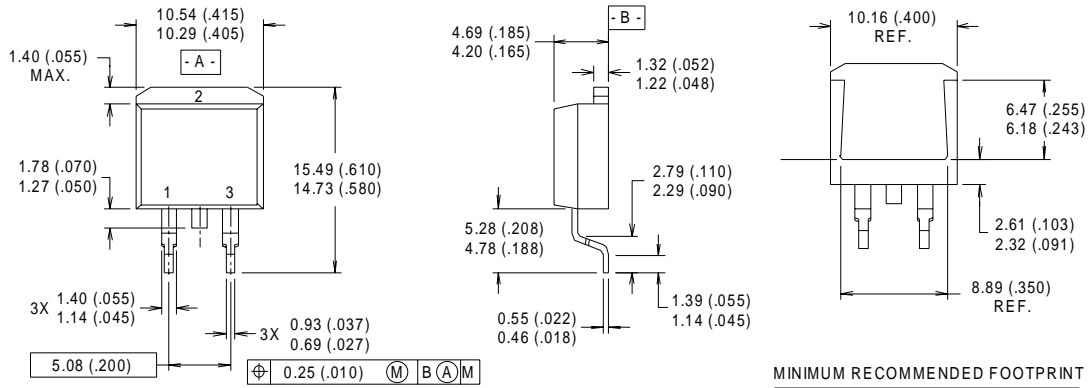
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

IRF640S/L

International
IOR Rectifier

D²Pak Package Outline



NOTES:

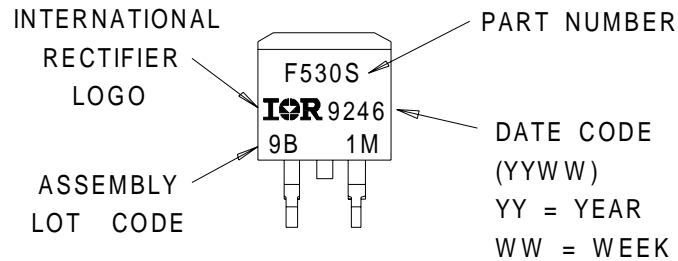
- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

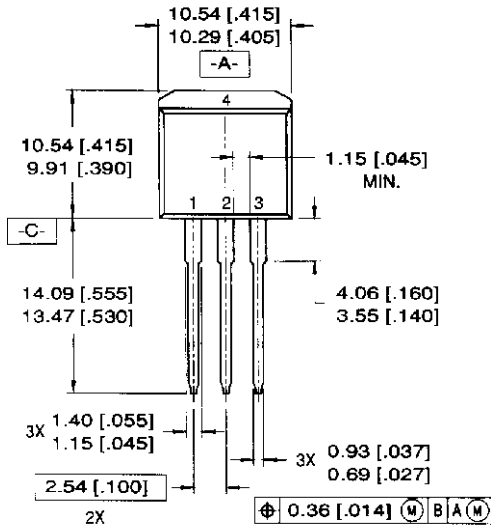
Part Marking Information

D²Pak



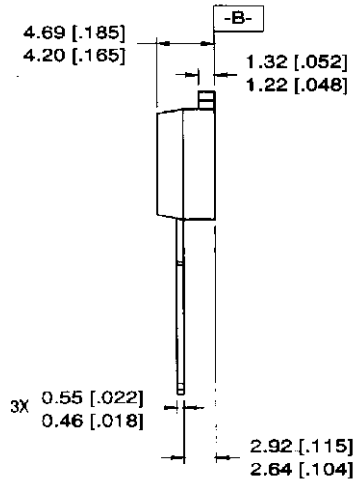
Package Outline

TO-262 Outline



LEAD ASSIGNMENTS

- | | |
|-----------|------------|
| 1 = GATE | 3 = SOURCE |
| 2 = DRAIN | 4 = DRAIN |



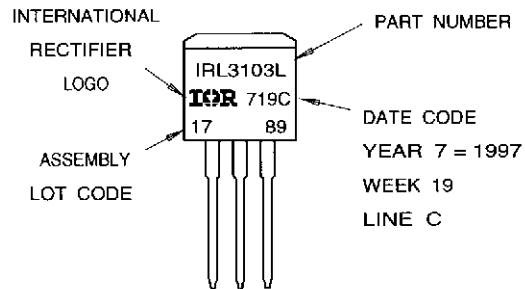
NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

Part Marking Information

TO-262

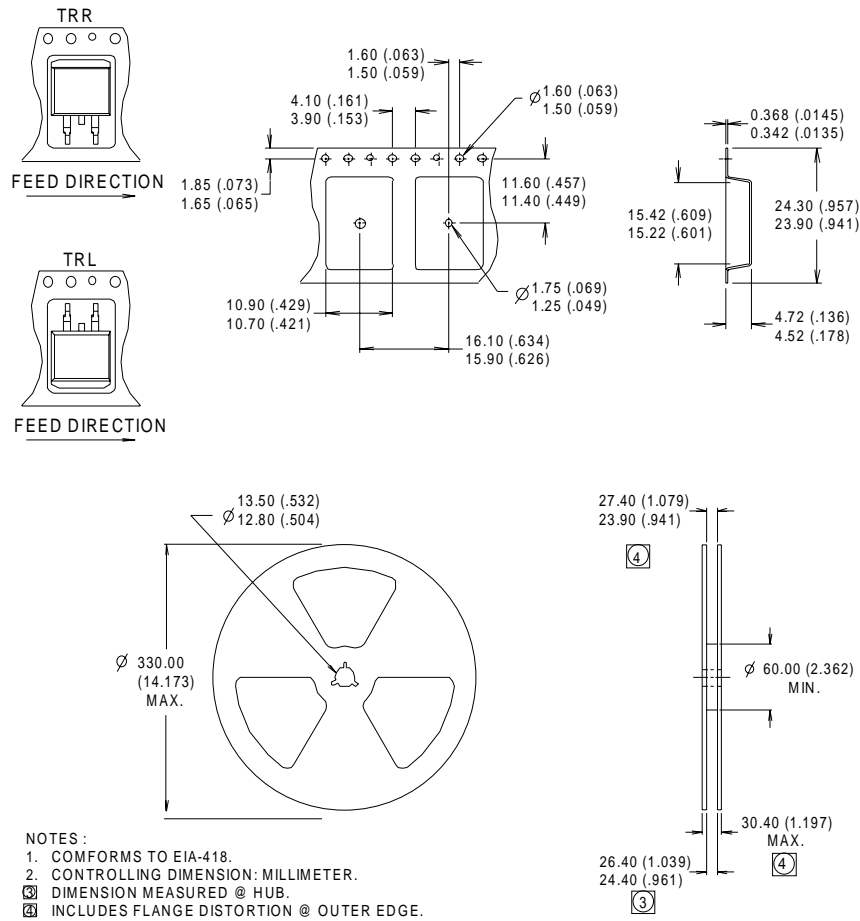
EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"



IRF640S/L

International
IR Rectifier

Tape & Reel Information D²Pak



International
IR Rectifier

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

IR GREAT BRITAIN: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 838 4630

IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936

Data and specifications subject to change without notice. 7/99



Notice

The products described herein were acquired by Vishay Intertechnology, Inc., as part of its acquisition of International Rectifier's Power Control Systems (PCS) business, which closed in April 2007. Specifications of the products displayed herein are pending review by Vishay and are subject to the terms and conditions shown below.

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.

International Rectifier®, IR®, the IR logo, HEXFET®, HEXSense®, HEXDIP®, DOL®, INTERO®, and POWIRTRAIN® are registered trademarks of International Rectifier Corporation in the U.S. and other countries. All other product names noted herein may be trademarks of their respective owners.